Supplementary information for:

Band Alignment and Interface Properties Enhancement for Heterojunction Solar Cell by Employing Amorphous-Nanocrystalline Hierarchical Emitter Layer

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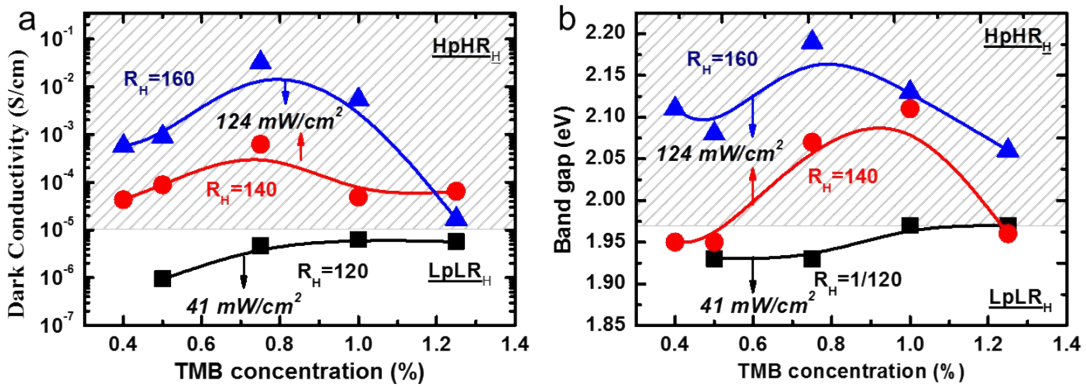

Fig. S1. (a) Dark conductivity and (b) band gap of p-type Si films deposited with various TMB concentrations.

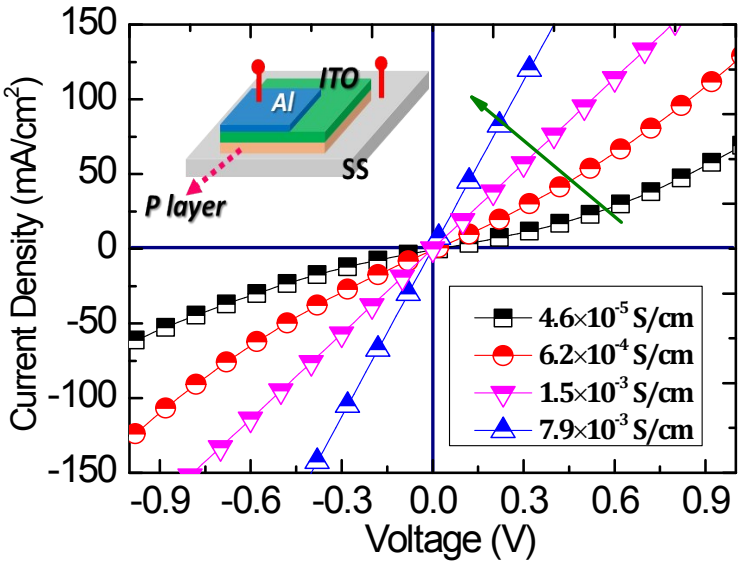

Fig. S2. J–V measurement results of the samples with SS / p layer / ITO / Al architecture. The conductivity of p layer was increased from 4.6×10^{-5} S/cm to 7.9×10^{-3} S/cm.